

ESD PROTECTION DIODE

Discription

The CPDQC12VE is designed to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time provide best in class protection on designs that are exposed to ESD. Because of its small size, it is suited for use in cellular phones, MP3 players, digital cameras and many other portable applications where board space is at a premium.

Applications

- Cellular phones audio
- I MP3 players
- I Digital cameras
- I Portable applicationss
- I mobile telephone

Features

- Small Body Outline Dimensions:
 1.00 mm x 0.60 mm
- Low Body Height: 0.50 mm
- Low Leakage
- Response Time is Typically < 1 ns
- ESD Rating of Class 3 (> 16 kV) per Human Body Model
- IEC61000-4-2 Level 4 ESD Protection
- We declare that the material of product compliance with RoHS requirements.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
IEC 61000-4-2 (ESD) Air Contact Contact discharge		±16 ±16	kV kV
ESD Voltage Per Human Body Model		16	kV
Total Power Dissipation on FR-5 Board (Note 1)	PD	200	mW
@ T _A =25℃			
Junction and Storage Temperature Range	TJ,TSTG	-55 to 150	°C
Lead Solder Temperature – Maximum (10	TL	260	°C
Second Duration)			

Stresses exceeding Maximum Ratings may damage the device. Maximum Rating are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR-5 = 1.0*0.75*0.62 in.



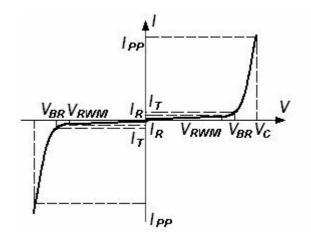
SOD882



ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted)

Symbol	Parameter			
IPP	Maximum Reverse Peak Pulse Current			
Vc	Clamping Voltage @ I _{PP}			
V _{RWM}	Working Peak Reverse Voltage			
I _R	Maximum Reverse Leakage Current @ V _{RW}			
VBR	Breakdown Voltage @ I _T			
IT	Test Current			
I _F	Forward Current			
VF	Forward Voltage @ I _F			
P _{pk}	Peak Power Dissipation			
C	Max. Capacitance @V _B = 0 and f = 1 MHz			



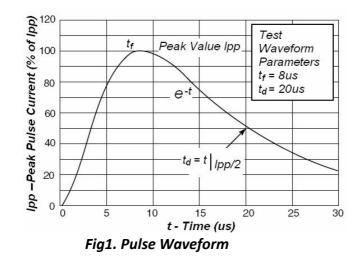
ELECTRICAL CHARACTERISTICS (T_A=25 $^\circ C$ unless otherwise noted, VF=0.9V Max. @ IF=10Ma for all types)

	V _{RWM}	I _R	V _{BR}	Ι _Τ	I _{PP}	Vc	P _{PK}	С
	(V)	(μA)	(V)	(mA)	(A)	(V)	(W)	(pF)
Device		@	@ I⊤			@ Max I _{PP}	(8*20 µs)	
		V_{RWM}	(Note 2)		(Note 3)	(Note 3)		
	Max	Max	Min		Max	Max	Max	Тур
CPDQC12VE	12	1.0	13.3	1.0	4	18	72	12.5

2. V_{BR} is measured with a pulse test current IT at an ambient temperature of 25 $^\circ\!\mathrm{C}$

3. Surge current waveform per Figure 3.

SXSEM



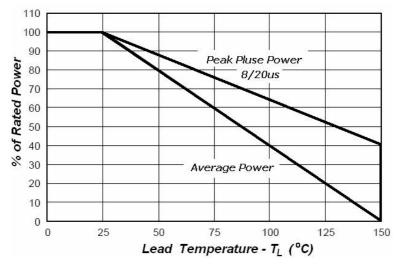
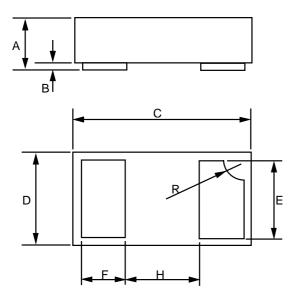


Fig Power Derating



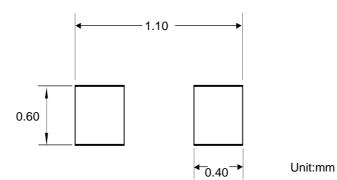
SOD882

DIMENSION OUTLINE:



Unit:mm

Dim	Inches		Millimeters		
	MIN	MAX	MIN	МАХ	
А	0.013	0.020	0.34	0.50	
В	0.000	0.002	0.00	0.05	
С	0.037	0.042	0.95	1.075	
D	0.021	0.026	0.55	0.675	
Е	0.017	0.021	0.45	0.55	
F	0.007	0.011	0.20	0.30	
Н	0.015Typ.		0.40Тур.		
R	0.001	0.005	0.05	0.15	



Rev.O 4/4